

Description

The TSV619x family of single and dual operational amplifiers offers low voltage, low power operation, and rail-to-rail input and output.

The devices also feature an ultra-low input bias current as well as a low input offset voltage.

The TSV619x have a gain bandwidth product of 450 kHz while consuming only 10 μ A at 5 V. They must be used in a gain configuration (equal or above 4 or -3).

These features make the TSV619x family ideal for sensor interfaces, battery supplied and portable applications, as well as active filtering.

Features

- Rail-to-rail input and output
- Low power consumption: 10 μ A typ at 5 V
- Low supply voltage: 1.5 to 5.5 V
- Gain bandwidth product: 450 kHz typ
- Stable when used in gain configuration
- Low input offset voltage: 800 μ V max (A version)
- Low input bias current: 1 pA typ
- Temperature range: -40 to 85 °C

Applications

- Battery-powered applications
- Smoke detectors
- Proximity sensors
- Portable devices
- Signal conditioning
- Active filtering
- Medical instrumentation

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1 Absolute maximum ratings and operating conditions

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage ⁽¹⁾	6	V
V_{id}	Differential input voltage ⁽²⁾	$\pm V_{CC}$	
V_{in}	Input voltage ⁽³⁾	$(V_{CC-}) - 0.2$ to $(V_{CC+}) + 0.2$	
T_{stg}	Storage temperature	-65 to 150	°C
R_{thja}	Thermal resistance junction to ambient ^{(4) (5)}		°C/W
	SC70-5	205	
	SOT23-5	250	
	MiniSO8	190	
	SO8	125	
T_j	Maximum junction temperature	150	°C
ESD	HBM: human body model ⁽⁶⁾	4	kV
	MM: machine model ⁽⁷⁾	200	V
	CDM: charged device model ⁽⁸⁾	1.5	kV
	Latch-up immunity	200	mA

1. All voltage values, except differential voltage are with respect to network ground terminal.
2. Differential voltages are the non-inverting input terminal with respect to the inverting input terminal.
3. V_{CC} - V_{in} must not exceed 6 V.
4. Short-circuits can cause excessive heating and destructive dissipation.
5. R_{th} are typical values.
6. Human body model: 100 pF discharged through a 1.5 kΩ resistor between two pins of the device, done for all couples of pin combinations with other pins floating.
7. Machine model: a 200 pF cap is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω), done for all couples of pin combinations with other pins floating.
8. Charged device model: all pins plus package are charged together to the specified voltage and then discharged directly to ground.

Table 2. Operating conditions

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage	1.5 to 5.5	V
V_{icm}	Common mode input voltage range	$(V_{CC-}) - 0.1$ to $(V_{CC+}) + 0.1$	
T_{oper}	Operating free air temperature range	-40 to 85	

2 Electrical characteristics

Table 3. Electrical characteristics at $V_{CC+} = 1.8$ V with $V_{CC-} = 0$ V, $V_{icm} = V_{CC}/2$, $T_{amb} = 25$ °C, and R_L connected to $V_{CC}/2$ (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
DC performance						
V_{io}	Offset voltage	TSV619x			4	mV
		TSV619xA			0.8	
$\Delta V_{io}/\Delta T$	Input offset voltage drift	$T_{min.} < T_{op} < T_{max.}$ TSV619x			5	$\mu V/^\circ C$
		$T_{min.} < T_{op} < T_{max.}$ TSV619xA			2	
I_{io}	Input offset current ($V_{out} = V_{cc}/2$)			1	10 ⁽¹⁾	pA
		$T_{min.} < T_{op} < T_{max.}$		1	25	
I_{ib}	Input bias current ($V_{out} = V_{cc}/2$)			1	10 ⁽¹⁾	pA
		$T_{min.} < T_{op} < T_{max.}$		1	25	
CMR	Common mode rejection ratio $20 \log (\Delta V_{ic}/\Delta V_{io})$	0 V to 1.8 V, $V_{out} = 0.9$ V	55	71		dB
		$T_{min.} < T_{op} < T_{max.}$	53			
A_{vd}	Large signal voltage gain	$R_L = 10 \text{ k}\Omega$ $V_{out} = 0.5$ V to 1.3 V	78	83		
		$T_{min.} < T_{op} < T_{max.}$	74			
V_{OH}	High level output voltage ($V_{OH} = V_{CC} - V_{out}$)	$R_L = 10 \text{ k}\Omega$ $T_{min.} < T_{op} < T_{max.}$		4	35	mV
V_{OL}	Low level output voltage	$R_L = 10 \text{ k}\Omega$ $T_{min.} < T_{op} < T_{max.}$		7	35	
I_{out}	I_{sink}	$V_o = 1.8$ V $T_{min.} < T_{op} < T_{max.}$	9	13		mA
	I_{source}	$V_o = 0$ V $T_{min.} < T_{op} < T_{max.}$	8	10		
I_{CC}	Supply current (per operator)	No load, $V_{out} = V_{cc}/2$	6.5	9	12	μA
		$T_{min.} < T_{op} < T_{max.}$	6		12.5	
AC performance						
GBP	Gain bandwidth product	$R_L = 10 \text{ k}\Omega$ $C_L = 20 \text{ pF}$		380		kHz
Gain	Minimum gain for stability	Phase margin = 60 °, $R_f = 10 \text{ k}\Omega$, $R_L = 10 \text{ k}\Omega$, $C_L = 20 \text{ pF}$, $T_{op} = 25$ °C		5		V/V
SR	Slew rate	$R_L = 10 \text{ k}\Omega$, $C_L = 20 \text{ pF}$, $V_{out} = 0.5$ V to 1.3 V		0.06		V/μs
e_n	Equivalent input noise voltage	$f = 1$ kHz		110		$\frac{nV}{\sqrt{\text{Hz}}}$
THD+N	Total harmonic distortion + noise	$F_{in} = 1$ kHz, $Av = 5$, $V_{out} = 1$ V _{pp} , $R_L = 100 \text{ k}\Omega$, $BW = 22$ kHz		0.1		%

1. Guaranteed by design.

Table 4. Electrical characteristics at $V_{CC+} = 3.3\text{ V}$, $V_{CC-} = 0\text{ V}$, $V_{icm} = V_{CC}/2$, $T_{amb} = 25^\circ\text{C}$, R_L connected to $V_{CC}/2$ (unless otherwise specified)

Symbol	Parameter		Min.	Typ.	Max.	Unit
DC performance						
V_{io}	Offset voltage	TSV619x			4	mV
		TSV619xA			0.8	
$\Delta V_{io}/\Delta T$	Input offset voltage drift	$T_{min} < T_{op} < T_{max}$ TSV619x			5	$\mu\text{V}/^\circ\text{C}$
		$T_{min} < T_{op} < T_{max}$ TSV619xA			2	
I_{io}	Input offset current			1	10 ⁽¹⁾	pA
		$T_{min.} < T_{op} < T_{max.}$		1	25	
I_{ib}	Input bias current			1	10 ⁽¹⁾	
		$T_{min.} < T_{op} < T_{max.}$		1	25	
CMR	Common mode rejection ratio $20 \log (\Delta V_{ic}/\Delta V_{io})$	0 V to 3.3 V, $V_{out} = 1.75\text{ V}$	61	76		dB
		$T_{min.} < T_{op} < T_{max.}$	58			
A_{vd}	Large signal voltage gain	$R_L = 10\text{ k}\Omega$, $V_{out} = 0.5\text{ V}$ to 2.8 V	85	92		
		$T_{min.} < T_{op} < T_{max.}$	83			
V_{OH}	High level output voltage ($V_{OH} = V_{CC} - V_{out}$)	$R_L = 10\text{ k}\Omega$ $T_{min.} < T_{op} < T_{max.}$		5	35	mV
V_{OL}	Low level output voltage	$R_L = 10\text{ k}\Omega$ $T_{min.} < T_{op} < T_{max.}$		10	35	
I_{out}	Isink	$V_o = V_{CC}$ $T_{min.} < T_{op} < T_{max.}$	37	44		mA
	Isource	$V_o = 0\text{ V}$ $T_{min.} < T_{op} < T_{max.}$	35			
I_{CC}	Supply current (per operator)	No load, $V_{out} = V_{CC}/2$	6.5	9.5	12.5	μA
		$T_{min.} < T_{op} < T_{max.}$	6		13	
AC performance						
GBP	Gain bandwidth product	$R_L = 10\text{ k}\Omega$ $C_L = 20\text{ pF}$		400		kHz
Gain	Minimum gain for stability	Phase margin = 60 °, $R_f = 10\text{k}\Omega$ $R_L = 10\text{ k}\Omega$ $C_L = 20\text{ pF}$, $T_{op} = 25^\circ\text{C}$		5		V/V
SR	Slew rate	$R_L = 10\text{ k}\Omega$ $C_L = 20\text{ pF}$, $V_{out} = 0.5\text{V}$ to 2.8V		0.07		V/ μs
e_n	Equivalent input noise voltage	$f = 1\text{ kHz}$		110		$\frac{\text{nV}}{\sqrt{\text{Hz}}}$

1. Guaranteed by design.

**Table 5. Electrical characteristics at $V_{CC+} = 5\text{ V}$, $V_{CC-} = 0\text{ V}$, $V_{icm} = V_{CC}/2$, $T_{amb} = 25^\circ\text{C}$,
 R_L connected to $V_{CC}/2$ (unless otherwise specified)**

Symbol	Parameter		Min.	Typ.	Max.	Unit
DC performance						
V_{io}	Offset voltage	TSV619x TSV619xA			4 0.8	mV
		$T_{min} < T_{op} < T_{max}$ TSV619x $T_{min} < T_{op} < T_{max}$ TSV619xA			5 2	
$\Delta V_{io}/\Delta T$	Input offset voltage drift			2		$\mu\text{V}/^\circ\text{C}$
I_{io}	Input offset current			1	$10^{(1)}$	pA
		$T_{min.} < T_{op} < T_{max.}$		1	25	
I_{ib}	Input bias current			1	$10^{(1)}$	pA
		$T_{min.} < T_{op} < T_{max.}$		1	25	
CMR	Common mode rejection ratio 20 log $(\Delta V_{ic}/\Delta V_{io})$	0 V to 5 V, $V_{out} = 2.5\text{ V}$	64	80		dB
		$T_{min.} < T_{op} < T_{max.}$	63			
SVR	Supply voltage rejection ratio 20 log $(\Delta V_{cc}/\Delta V_{io})$	$V_{cc} = 1.8$ to 5 V	76	93		dB
		$T_{min.} < T_{op} < T_{max.}$	74			
A_{vd}	Large signal voltage gain	$R_L = 10\text{ k}\Omega$ $V_{out} = 0.5\text{ V}$ to 4.5 V	88	93		
		$T_{min.} < T_{op} < T_{max.}$	85			
V_{OH}	High level output voltage ($V_{OH} = V_{CC} - V_{out}$)	$R_L = 10\text{ k}\Omega$ $T_{min.} < T_{op} < T_{max.}$		7	35 50	mV
V_{OL}	Low level output voltage	$R_L = 10\text{ k}\Omega$ $T_{min.} < T_{op} < T_{max.}$		16	35 50	
I_{out}	Isink	$V_o = V_{CC}$ $T_{min.} < T_{op} < T_{max.}$	52 42	57		mA
	Isource	$V_o = 0\text{ V}$ $T_{min.} < T_{op} < T_{max.}$	58 49	63		
I_{CC}	Supply current (per operator)	No load, $V_{out} = V_{CC}/2$	7.5	10.5	14	μA
		$T_{min.} < T_{op} < T_{max.}$	7		15	
AC performance						
GBP	Gain bandwidth product	$R_L = 10\text{ k}\Omega$ $C_L = 20\text{ pF}$		450		kHz
Gain	Minimum gain for stability	Phase margin = 60 °, $R_f = 10\text{k}\Omega$, $R_L = 10\text{ k}\Omega$ $C_L = 20\text{ pF}$, $T_{op} = 25^\circ\text{C}$		5		V/V
SR	Slew rate	$R_L = 10\text{ k}\Omega$ $C_L = 20\text{ pF}$, $V_{out} = 0.5\text{V}$ to 4.5V		0.08		V/ μs
e_n	Equivalent input noise voltage	$f = 1\text{ kHz}$		105		$\frac{\text{nV}}{\sqrt{\text{Hz}}}$
THD+N	Total harmonic distortion + noise	$F_{in} = 1\text{ kHz}$, $Av = 5$, $V_{out} = 1\text{ V}_{pp}$, $R_L = 100\text{ k}\Omega$ BW = 22kHz		0.1		%

1. Guaranteed by design.

Figure 1. Supply current vs. supply voltage at $V_{icm} = V_{CC}/2$

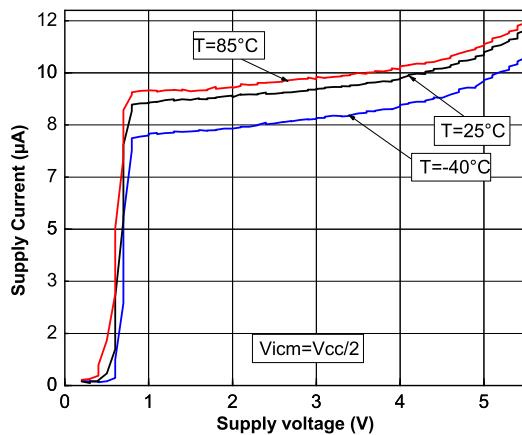


Figure 2. Output current vs. output voltage at $V_{CC} = 1.5$ V

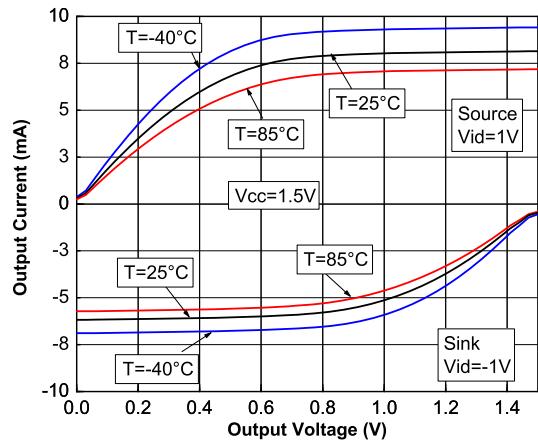


Figure 3. Output current vs. output voltage at $V_{CC} = 5$ V

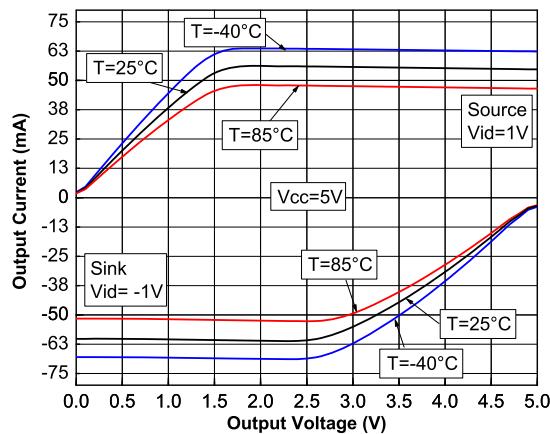


Figure 4. Voltage gain and phase vs. frequency at $V_{CC} = 1.5$ V

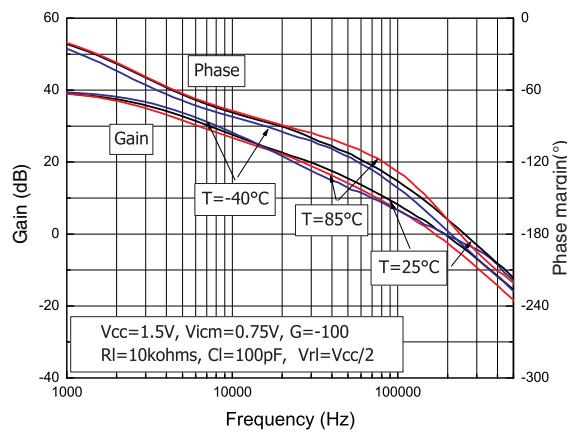


Figure 5. Voltage gain and phase vs. frequency at $V_{CC} = 5$ V

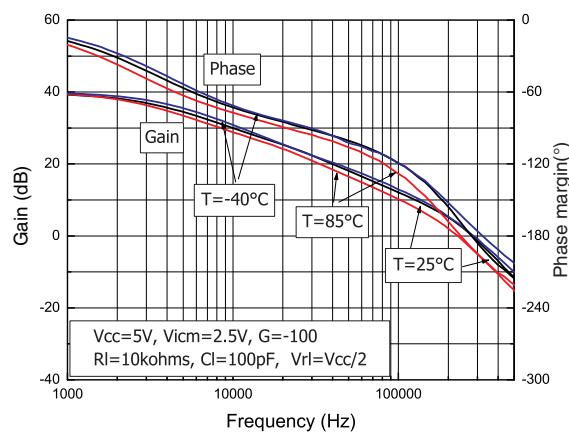


Figure 6. Positive slew rate vs. time at $V_{CC} = 1.5$ V

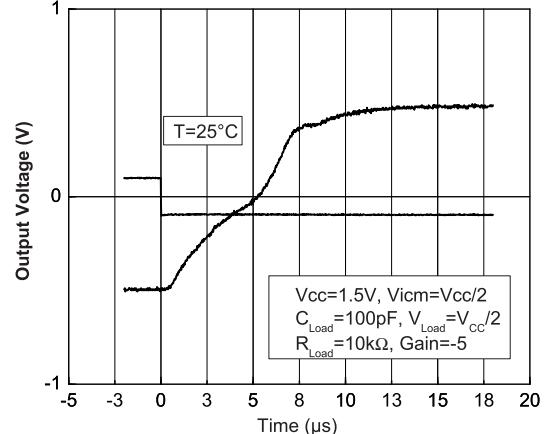


Figure 7. Negative slew rate vs. time at $V_{CC} = 1.5\text{ V}$

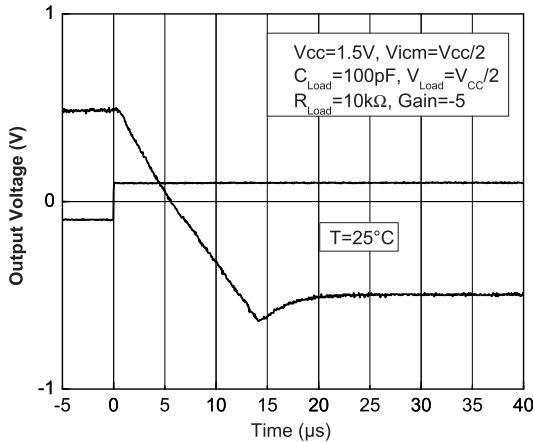


Figure 8. Positive slew rate vs. time at $V_{CC} = 5.5\text{ V}$

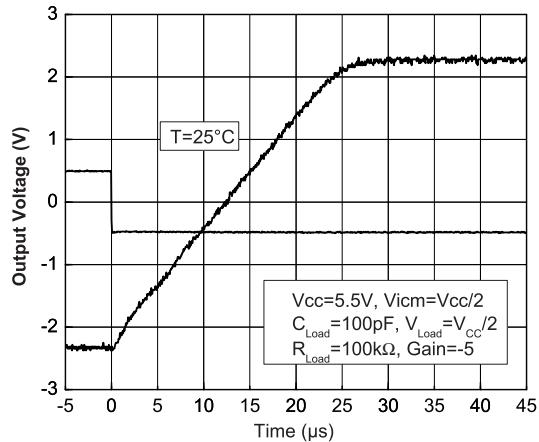


Figure 9. Negative slew rate vs. time, $V_{CC} = 5.5\text{ V}$, $C_{Load} = 100\text{ pF}$, $R_{Load} = 100\text{ k}\Omega$

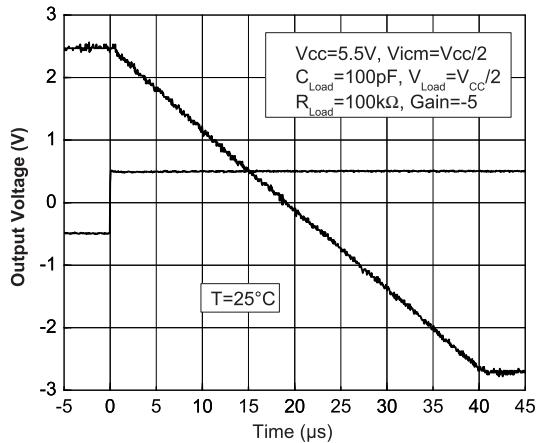


Figure 10. Noise vs. frequency at $V_{CC} = 5\text{ V}$, $T = 25^\circ\text{C}$

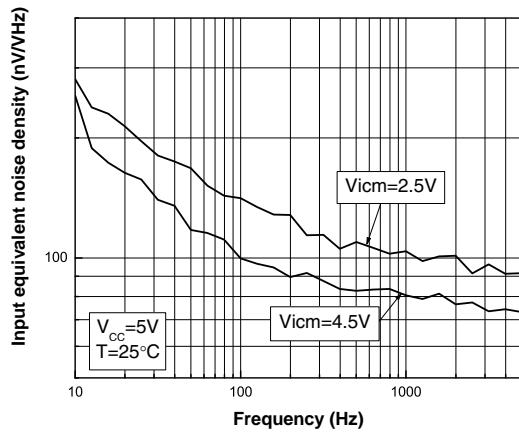


Figure 11. Distortion + noise vs. frequency

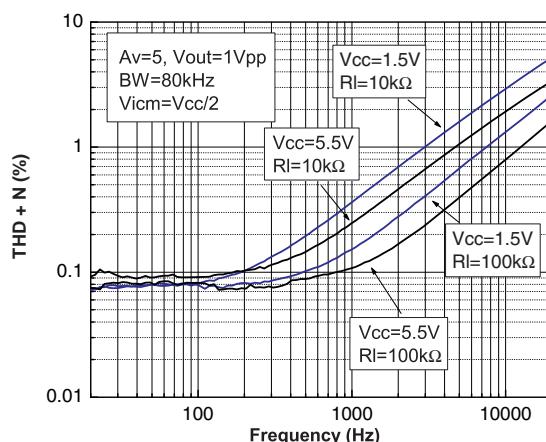
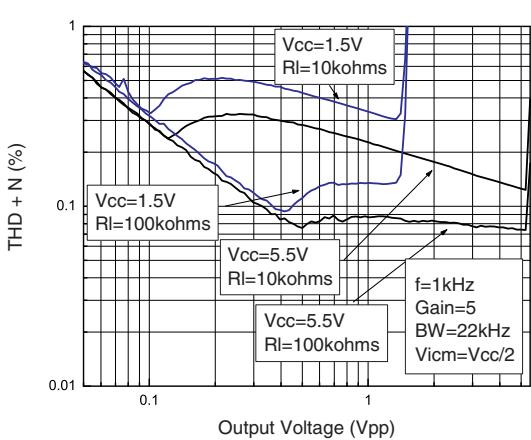


Figure 12. Distortion + noise vs. output voltage



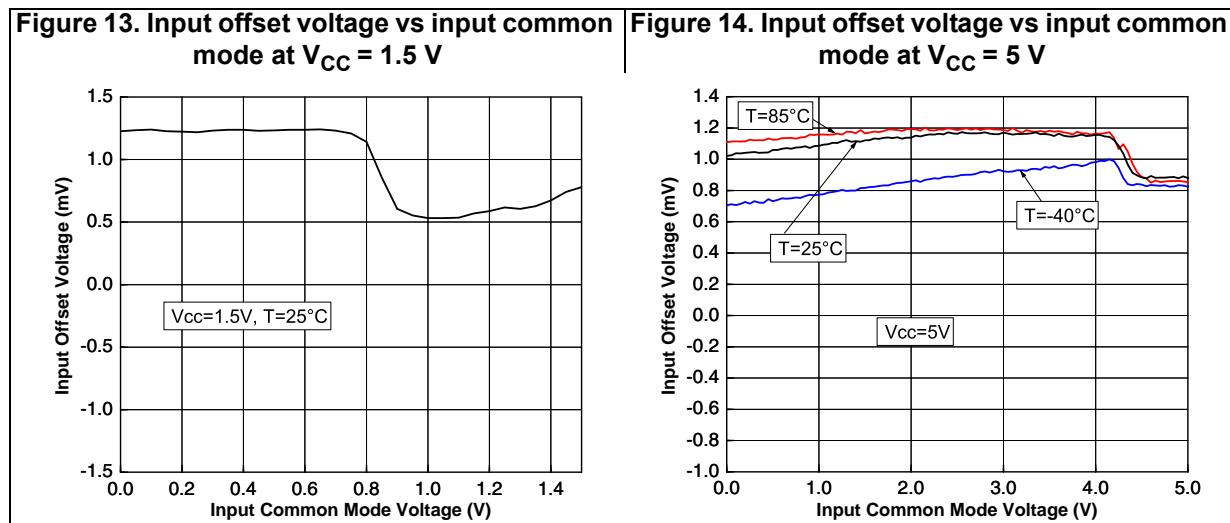
3 Application information

3.1 Operating voltages

The TSV619x can operate from 1.5 to 5.5 V. Their parameters are fully specified for 1.8, 3.3, and 5 V power supplies. However, the parameters are very stable in the full V_{CC} range and several characterization curves show the TSV619x characteristics at 1.5 V. Additionally, the main specifications are guaranteed in extended temperature ranges from -40 °C to 85 °C.

3.2 Rail-to-rail input

The TSV619x are built with two complementary PMOS and NMOS input differential pairs. The devices have a rail-to-rail input, and the input common mode range is extended from $V_{CC-} - 0.1$ V to $V_{CC+} + 0.1$ V. The transition between the two pairs appears at $V_{CC+} - 0.7$ V. In the transition region, the performance of CMRR, PSRR, V_{IO} and THD is slightly degraded (as shown in [Figure 13](#) and [Figure 14](#) for V_{IO} vs. V_{ICM}).



The device is guaranteed without phase reversal.

3.3 Rail-to-rail output

The operational amplifiers' output levels can go close to the rails: less than 35 mV above GND rail and less than 35 mV below V_{CC} rail when connected to 10 kΩ load to $V_{CC}/2$.

3.4 PCB layouts

For correct operation, it is advised to add 10 nF decoupling capacitors as close as possible to the power supply pins.

3.5 Macromodel

An accurate macromodel of the TSV619x is available on STMicroelectronics' web site at www.st.com. This model is a trade-off between accuracy and complexity (that is, time simulation) of the TSV619x operational amplifiers. It emulates the nominal performances of a typical device within the specified operating conditions mentioned in the datasheet. It also helps to validate a design approach and to select the right operational amplifier, *but it does not replace on-board measurements.*

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.
ECOPACK® is an ST trademark.

4.1 SOT23-5 package information

Figure 15. SOT23-5 package outline

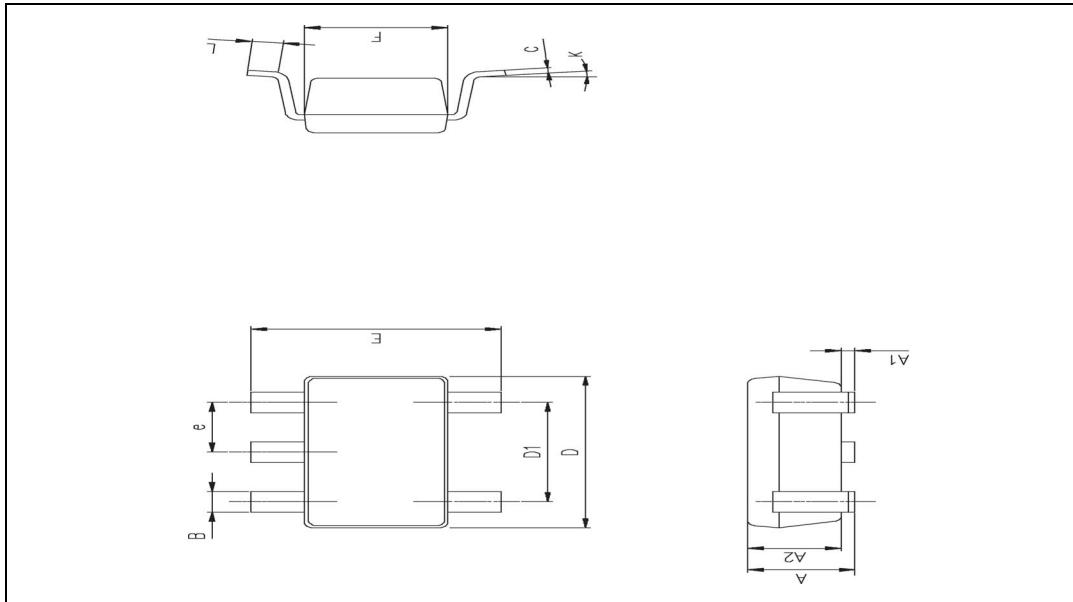


Table 6. SOT23-5 mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.90	1.20	1.45	0.035	0.047	0.057
A1			0.15			0.006
A2	0.90	1.05	1.30	0.035	0.041	0.051
B	0.35	0.40	0.50	0.013	0.015	0.019
C	0.09	0.15	0.20	0.003	0.006	0.008
D	2.80	2.90	3.00	0.110	0.114	0.118
D1		1.90			0.075	
e		0.95			0.037	
E	2.60	2.80	3.00	0.102	0.110	0.118
F	1.50	1.60	1.75	0.059	0.063	0.069
L	0.10	0.35	0.60	0.004	0.013	0.023
K	0 degrees		10 degrees			

4.2 SC70-5 (SOT323-5) package information

Figure 16. SC70-5 (SOT323-5) package outline

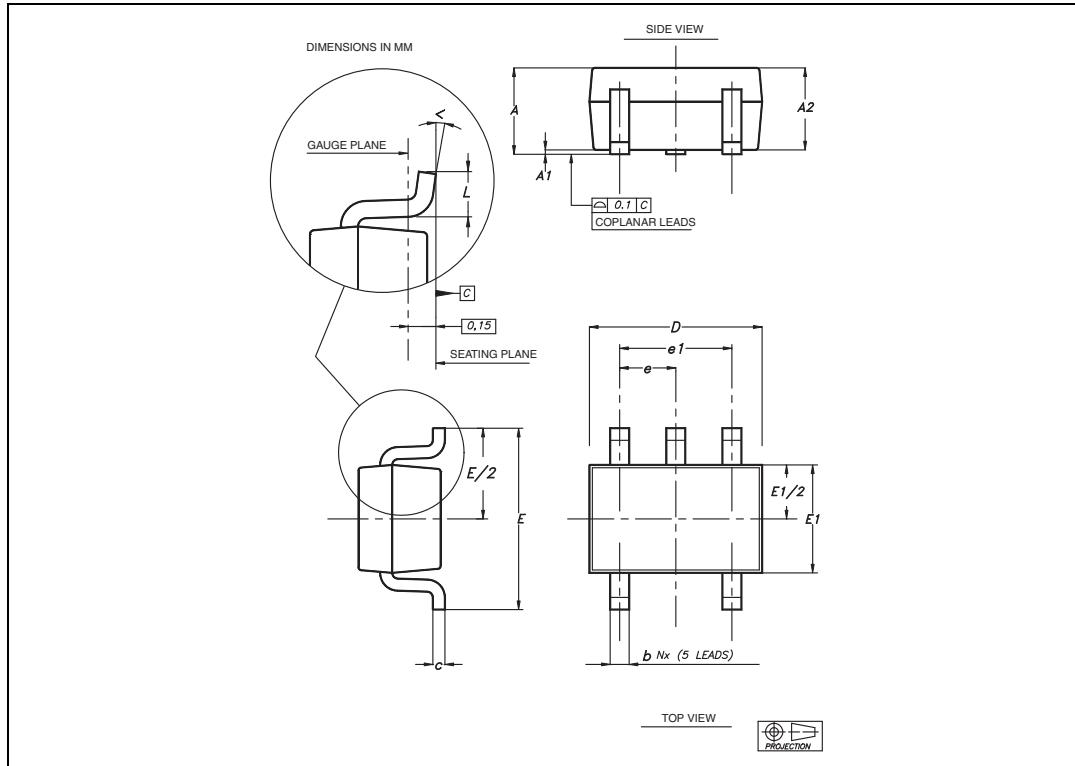


Table 7. SC70-5 (SOT323-5) mechanical data

Ref	Dimensions					
	Millimeters			Inches		
	Min	Typ	Max	Min	Typ	Max
A	0.80		1.10	0.315		0.043
A1			0.10			0.004
A2	0.80	0.90	1.00	0.315	0.035	0.039
b	0.15		0.30	0.006		0.012
c	0.10		0.22	0.004		0.009
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.80	2.10	2.40	0.071	0.083	0.094
E1	1.15	1.25	1.35	0.045	0.049	0.053
e		0.65			0.025	
e1		1.30			0.051	
L	0.26	0.36	0.46	0.010	0.014	0.018
<	0°		8°			

4.3 SO8 package information

Figure 17. SO8 package outline

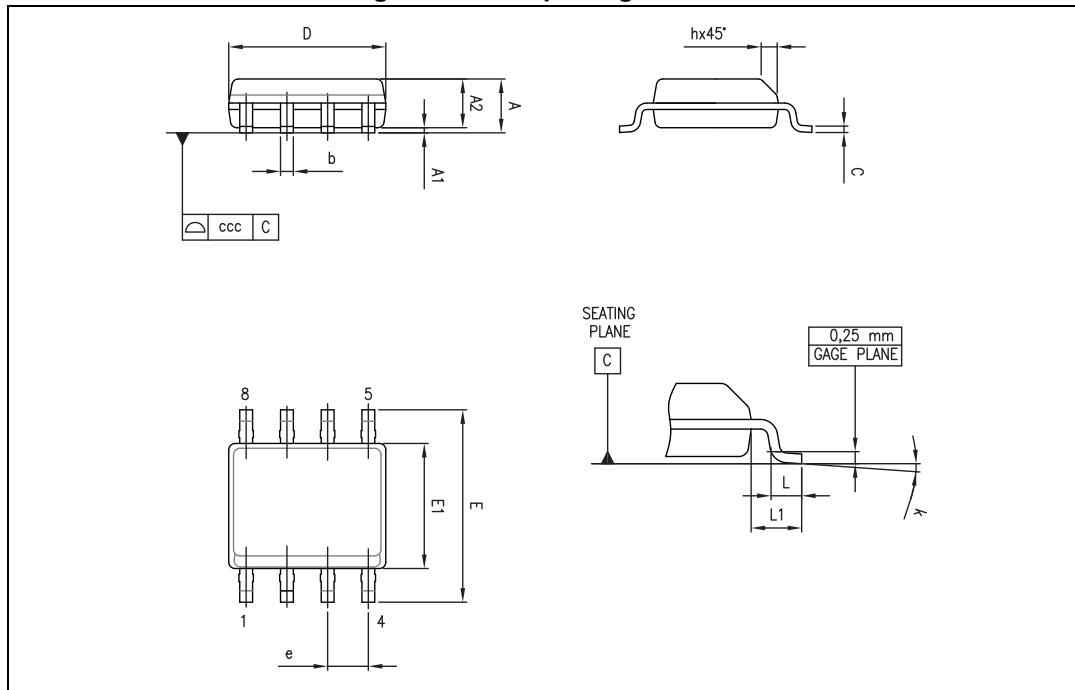


Table 8. SO8 mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
A1	0.10		0.25	0.004		0.010
A2	1.25			0.049		
b	0.28		0.48	0.011		0.019
c	0.17		0.23	0.007		0.010
D	4.80	4.90	5.00	0.189	0.193	0.197
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e		1.27			0.050	
h	0.25		0.50	0.010		0.020
L	0.40		1.27	0.016		0.050
L1		1.04			0.040	
k	1°		8°	1°		8°
ccc			0.10			0.004

4.4 MiniSO8 package information

Figure 18. MiniSO8 package outline

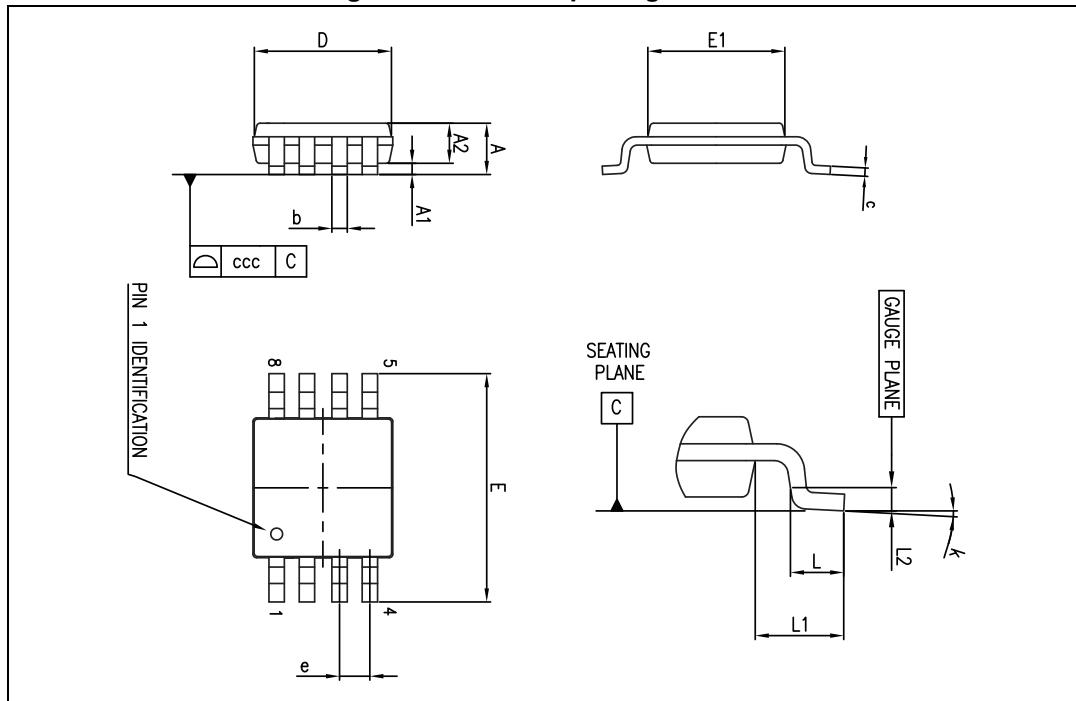


Table 9. MiniSO8 mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.1			0.043
A1	0		0.15	0		0.006
A2	0.75	0.85	0.95	0.030	0.033	0.037
b	0.22		0.40	0.009		0.016
c	0.08		0.23	0.003		0.009
D	2.80	3.00	3.20	0.11	0.118	0.126
E	4.65	4.90	5.15	0.183	0.193	0.203
E1	2.80	3.00	3.10	0.11	0.118	0.122
e		0.65			0.026	
L	0.40	0.60	0.80	0.016	0.024	0.031
L1		0.95			0.037	
L2		0.25			0.010	
k	0°		8°	0°		8°
ccc			0.10			0.004

5 Ordering information

Table 10. Order codes

Order code	Temperature range	Package	Packing	Marking
TSV6191ILT	-40 °C to 85 °C	SOT23-5	Tape and reel	K110
TSV6191AILT		SC70-5		K115
TSV6191ICT		SO-8		K10
TSV6191AICT		MiniSO-8		K13
TSV6192IDT				V6192I
TSV6192AIDT				V6192AI
TSV6192IST				K130
TSV6192AIST				K129

6 Revision history

Table 11. Document revision history

Date	Revision	Changes
04-Oct-2010	1	Initial release.
16-May-2017	2	<i>Table 3, Table 4, and Table 5:</i> changed "DV _{IO} to $\Delta V_{IO}/\Delta T$, updated VOH parameter information, changed min. values for VOH parameter to max. values. <i>Table 10: Order codes:</i> removed obsolete order codes TSV6192ID and TSV6192AID